PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OF 1573822

In re the Application of

IAP5 Rec'd PCT/PTO 28 MAR 2006

Ryoji HOSHI et al.

Application No.: New U.S. National Stage of PCT/JP2004/015395

Filed: March 28, 2006 Docket No.: 127516

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of one or more non-English language reference is discussed in the present specification. See References <u>6-9</u>.
- 3. One or more reference cited herein was cited in the International Search Report.
 An English language version of the International Search Report is attached for the Examiner's information. See References <u>1-6</u>.
- 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- 5. An English language Abstract of one or more non-English language reference is attached hereto. See References <u>2-8</u>.
- 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See References 2-8.

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7. Reference 1 corresponds to Reference 5.

10/573822

Respectfully submitted,

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WPB:DAT/nxy

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Date: March 28, 2006

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Form PTO-1449 US Dept. of Commerce ATTY DOCKET NO. APPLICATION NO. PATENT & TRADEMARK OFFICE New U.S. National 127516 (REV. 1/06) 10/573822 Stage of PCT/JP2004/015395 INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) **APPLICANTS** Ryoji HOSHI et al. FILING DATE March 28, 2006 U.S. PATENT DOCUMENTS Cite Examiner Document Number Date Name Initials No. US 2002/0017234 A1 02/14/2002 ONO et al. FOREIGN PATENT DOCUMENTS With With Examiner Cite Initials No. Document Number Date Country English English Abstract Translation 2. JP-A-07-223893 08/22/1995 **JAPAN** Х 3. JP-A-08-157293 06/18/1996 **JAPAN** Х \mathbf{x} х 02/16/1999 **JAPAN** \mathbf{x} 4. JP-A-11-043397 JP-A-2002-012498 01/15/2002 **JAPAN** Х X 5. 6. JP-A-2002-226296 08/14/2002 **JAPAN** X Х \mathbf{x} 7. JP-A-08-330316 12/13/1996 **JAPAN** X 03/23/1999 **JAPAN** Х х 8. JP-A-11-079889 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) Examiner Cite Initials No.

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	9.	D.T.J. HURLE et al.; "Mechanism of Swirl Defects Formation in Silicon"; Journal of Crystal Growth; Vol. 59; 1982;
		pp. 625-643.
EXAMINER		DATE CONSIDERED

and not considered. Include copy of this form with next communication to applicant.

Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance

Date: March 28, 2006

Examiner: